

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L88	7	((ndr or pin or p-i-n or p/i/n) near diode) same memory same (node)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/27 14:05
L89	7	((ndr or pin or p-i-n or p/i/n or nip or n-i-p or n/i/p) near diode) same memory same (node)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/27 14:05
L90	11	((ndr or pin or p-i-n or p/i/n or nip or n-i-p or n/i/p or (negative ner differential near resistance)) near diode) same memory same (node)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/27 14:08
L91	15607	((ndr or pin or p-i-n or p/i/n or nip or n-i-p or n/i/p or (negative ner differential near resistance)) near diode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/27 14:07

EAST Search History

L116	63	I103 and ((ndr or pin or p-i-n or p/i/n or nip or n-i-p or n/i/p or (negative near differential near resistance)) near diode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/27 14:08
L117	12	I103 and ((ndr or pin or p-i-n or p/i/n or nip or n-i-p or n/i/p or (negative near differential near resistance)) near diode).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/27 14:10
L118	9	I103 and ((ndr or pin or p-i-n or p/i/n or nip or n-i-p or n/i/p or (negative near differential near resistance)) near diode) and (access near transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/27 14:17
L119	9	I103 and ((ndr or pin or p-i-n or p/i/n or nip or n-i-p or n/i/p or (negative near differential near resistance)) near diode) and (access near transistor) and (bit near line) and (word near line)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/27 14:18
L120	68	I103 and ((operate or operating or operated or operation) near10 diode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/27 14:19
L121	19	I103 and ((operate or operating or operated or operation) near10 diode with (ndr or (negative near differential)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/27 15:15
L122	0	I103 and ((operate or operating or operated or operation) near10 diode with (ndr or (negative near differential))) and (pin or p/i/n or p-i-n or n-i-p or n/i/p)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/27 15:16
L123	32	I103 and (pin or p/i/n or p-i-n or n-i-p or n/i/p)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/27 15:21
L124	10	I103 and (pin or p/i/n or p-i-n or n-i-p or n/i/p) and (ndr or (negative near differential near resistance))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/27 15:18

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L125	47	((pin or p/i/n or p-i-n or n-i-p or n/i/p) near2 diode) and (ndr or (negative near differential))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/27 15:23
L126	12	((pin or p/i/n or p-i-n or n-i-p or n/i/p) near2 diode) same (ndr or (negative near differential))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/27 15:24
L127	47	((pin or p/i/n or p-i-n or n-i-p or n/i/p) near2 diode) and (ndr or (negative near differential))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/27 15:41
L128	3	((pin or p/i/n or p-i-n or n-i-p or n/i/p) near2 diode) and (ndr or (negative near differential)) and (intrinsic near region)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/27 15:41
L129	9	((pin or p/i/n or p-i-n or n-i-p or n/i/p) near2 diode) and (ndr or (negative near differential)) and intrinsic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/27 15:42
L130	3	((pin or p/i/n or p-i-n or n-i-p or n/i/p) near2 diode) and (ndr or (negative near differential)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/27 15:43
L131	47	((pin or p/i/n or p-i-n or n-i-p or n/i/p) near2 diode) and (ndr or (negative near differential)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/27 15:43
L132	3	((pin or p/i/n or p-i-n or n-i-p or n/i/p) near2 diode) near10 (ndr or (negative near differential)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/27 15:44
L133	3	((pin or p/i/n or p-i-n or n-i-p or n/i/p) near2 diode) with (ndr or (negative near differential)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/27 15:44
L134	12	((pin or p/i/n or p-i-n or n-i-p or n/i/p) near2 diode) same (ndr or (negative near differential)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/27 15:45

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L135	47	((pin or p/i/n or p-i-n or n-i-p or n/i/p) near2 diode) and (ndr or (negative near differential)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/27 15:47
L136	1235	((pin or p/i/n or p-i-n or n-i-p or n/i/p) near2 diode) or (ndr or (negative near differential))) same intrinsic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/27 15:47
L137	1235	((pin or p/i/n or p-i-n or n-i-p or n/i/p) near2 diode) or (ndr or (negative near differential))) same intrinsic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/27 15:48
L138	1193	((pin or p/i/n or p-i-n or n-i-p or n/i/p) near2 diode) or (diode near10 (ndr or (negative near differential)))) same intrinsic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/27 15:48
L139	22	((pin or p/i/n or p-i-n or n-i-p or n/i/p) near2 diode) or (diode near10 (ndr or (negative near differential)))) same intrinsic same memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/27 15:48

EAST Search History

L152	94	l151 and (soi or (silicon near on near insulator))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/27 16:14
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